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1. (Thrice amended) A process of PECVD deposition comprising the steps of:
providing an ion promoting atmosphere; and
contacting a substrate with a plasma of approximately 50 to 90 % of a metal-containing gas in said ion promoting atmosphere.
2. The process of claim 1 wherein said step of providing an ion promoting atmosphere comprises selecting said ion atmosphere from a group consisting of nitrogen gas, argon gas, neon gas, krypton gas, xenon gas, helium gas and radon gas.
3. The process of claim 1 wherein said step of contacting a substrate with a plasma comprises having a temperature range of approximately 150 to 500 degrees Celsius.
4. (Once amended) The process of claim 1 wherein said step of contacting a substrate with a plasma comprises having a pressure range of 1 mTorr to 10 Torr.

CLAIMS 5-28 ARE CANCELED.

29. (Once amended) A process for PECVD deposition of metal-containing films on a surface, the process comprising:
maintaining a pressure and a temperature which allow for PECVD metal-containing film deposition; and
contacting said surface with a plasma of approximately 50 to 90% metal-containing compound in a chemically inert atmosphere.

CLAIMS 30-66 ARE CANCELED.

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